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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	CANbus, I²C, SCI, SPI, USB OTG
Peripherals	LVD, PWM, WDT
Number of I/O	66
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf51jm128evlk

1 MCF51JM128 Family Configurations

1.1 Device Comparison

The MCF51JM128 series consists of the devices compared in Table 1.

Table 1. MCF51JM128 Series Device Comparison

Feature	MCF51JM128			MCF51JM64			MCF51JM32		
	80-pin	64-pin	44-pin	80-pin	64-pin	44-pin	80-pin	64-pin	44-pin
Flash memory size (KB)	128			64			32		
RAM size (KB)	16			16			16		
V1 ColdFire core with BDM (background debug module)	Yes								
ACMP (analog comparator)	Yes								
ADC channels (12-bit)	12		8	12		8	12		8
CAN (controller area network)	Yes	Yes	No	Yes	Yes	No	Yes	Yes	No
RNGA + CAU	Yes[1]								
CMT (carrier modulator timer)	Yes								
COP (computer operating properly)	Yes								
IIC1 (inter-integrated circuit)	Yes								
IIC2	Yes	No		Yes	No		Yes	No	
IRQ (interrupt request input)	Yes								
KBI (keyboard interrupts)	8	8	6	8	8	6	8	8	6
LVD (low-voltage detector)	Yes								
MCG (multipurpose clock generator)	Yes								
Port I/O[2]	66	51	33	66	51	33	66	51	33
RGPIO (rapid general-purpose I/O)	16	6	0	16	6	0	16	6	0
RTC (real-time counter)	Yes								
SCI1 (serial communications interface)	Yes								
SCI2	Yes								
SPI1 (serial peripheral interface)	Yes								
SPI2	Yes								
TPM1 (timer/pulse-width modulator) channels	6	6	4	6	6	4	6	6	4
TPM2 channels	2								
USBOTG (USB On-The-Go dual-role controller)	Yes								
XOSC (crystal oscillator)	Yes								

1 Only existed on special part number

- RTC
  - 8-bit modulus counter with binary- or decimal-based prescaler
  - External clock source for precise time base, time-of-day, calendar or task scheduling functions
  - Free running on-chip low power oscillator (1 kHz) for cyclic wake-up without external components
- Carrier modulator timer (CMT)
  - carrier generator, modulator, and transmitter drive the infrared out (IRO) pin
  - operation in independent high/low time control, baseband, FSK, and direct IRO control modes
- Input/Output
  - 66 GPIOs
  - Eight keyboard interrupt pins with selectable polarity
  - Hysteresis and configurable pull-up device on all input pins; configurable slew rate and drive strength on all output pins
  - 16 bits of Rapid GPIO connected to the processor's local 32-bit platform bus with set, clear, and faster toggle functionality

1.4 Part Numbers

Table 3. Orderable Part Number Summary

Freescale Part Number	Description	Flash / SRAM (KB)	Package	Temperature
MCF51JM128EVLK	MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled	128 / 16	80 LQFP	–40 to +105 °C
MCF51JM128VLK	MCF51JM128 ColdFire Microcontroller	128 / 16	80 LQFP	–40 to +105 °C
MCF51JM128EVLH	MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled	128 / 16	64 LQFP	–40 to +105 °C
MCF51JM128VLH	MCF51JM128 ColdFire Microcontroller	128 / 16	64 LQFP	–40 to +105 °C
MCF51JM128EVQH	MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled	128 / 16	64 QFP	–40 to +105 °C
MCF51JM128VQH	MCF51JM128 ColdFire Microcontroller	128 / 16	64 QFP	–40 to +105 °C
MCF51JM128EVLD	MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled	128 / 16	44 LQFP	–40 to +105 °C
MCF51JM128VLD	MCF51JM128 ColdFire Microcontroller	128 / 16	44 LQFP	–40 to +105 °C
MCF51JM64EVLK	MCF51JM64 ColdFire Microcontroller with CAU and RNGA Enabled	64 / 16	80 LQFP	–40 to +105 °C
MCF51JM64VLK	MCF51JM64 ColdFire Microcontroller	64 / 16	80 LQFP	–40 to +105 °C
MCF51JM64EVLH	MCF51JM64 ColdFire Microcontroller with CAU and RNGA Enabled	64 / 16	64 LQFP	–40 to +105 °C
MCF51JM64VLH	MCF51JM64 ColdFire Microcontroller	64 / 16	64 LQFP	–40 to +105 °C
MCF51JM64EVQH	MCF51JM64 ColdFire Microcontroller with CAU and RNGA Enabled	64 / 16	64 QFP	–40 to +105 °C
MCF51JM64VQH	MCF51JM64 ColdFire Microcontroller	64 / 16	64 QFP	–40 to +105 °C

1.5 Pinouts and Packaging

Figure 2 shows the pinout of the 80-pin LQFP.

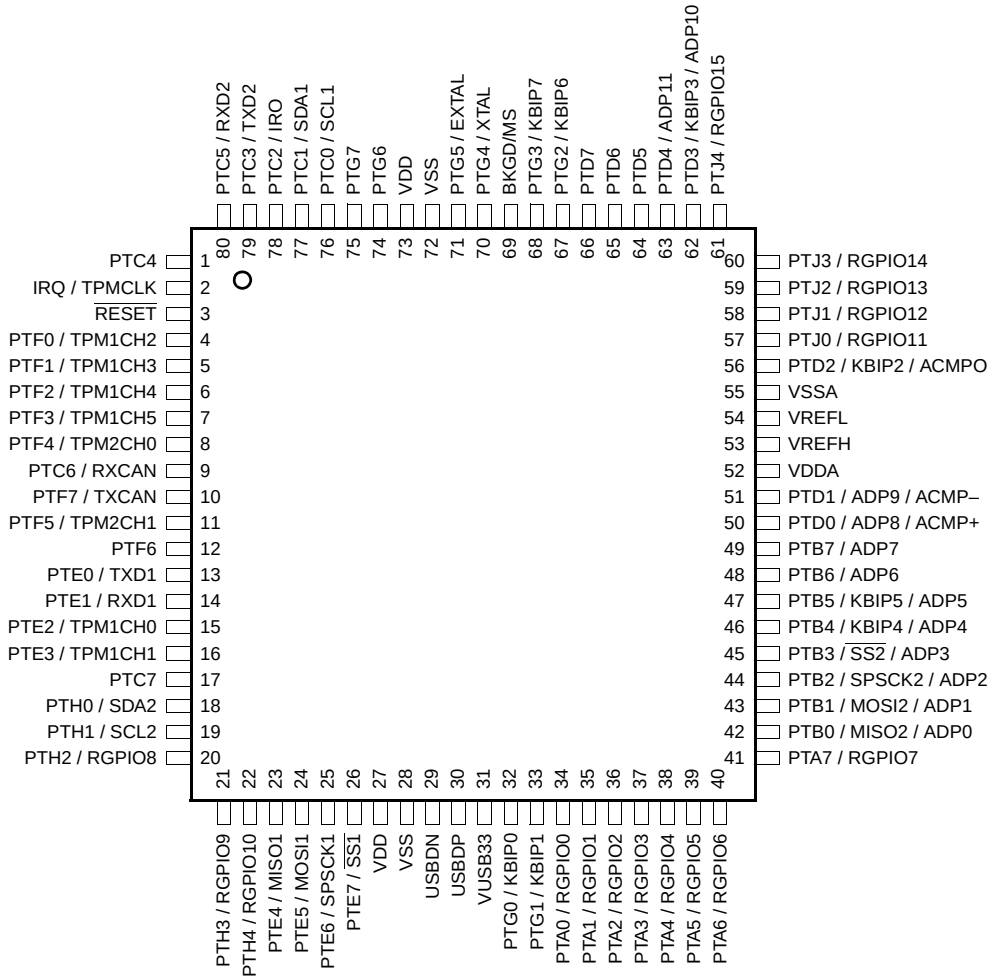


Figure 2. 80-pin LQFP

Figure 3 shows the pinout of the 64-pin LQFP and QFP.

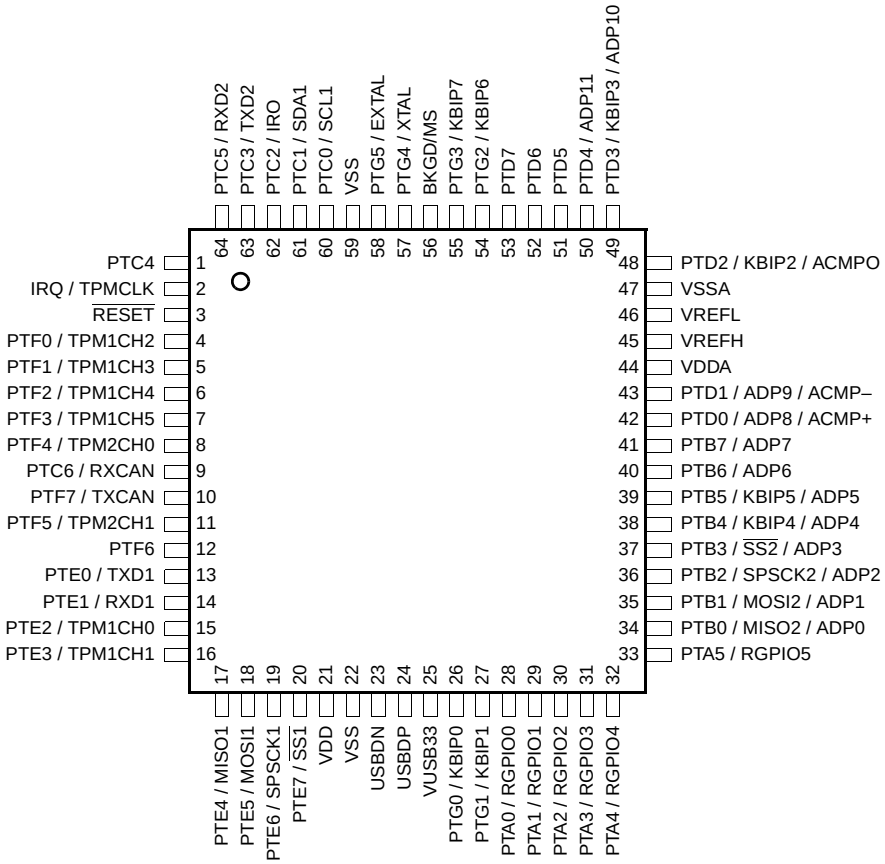


Figure 3. 64-pin QFP and LQFP

Table 4. Pin Assignments by Package and Pin Sharing Priority (continued)

Pin Number			<-- Lowest **Priority** --> Highest		
80	**64**	**44**	**Port Pin**	**Alt 1**	**Alt 2**
16	16	11	PTE3	TPM1CH1	—
17	—	—	PTC7	—	—
18	—	—	PTH0	SDA2	—
19	—	—	PTH1	SCL2	—
20	—	—	PTH2	RGPIO8	—
21	—	—	PTH3	RGPIO9	—
22	—	—	PTH4	RGPIO10	—
23	17	12	PTE4	MISO1	—
24	18	13	PTE5	MOSI1	—
25	19	14	PTE6	SPSCK1	—
26	20	15	PTE7	$\overline{SS1}$	—
27	21	16	—	—	VDD
28	22	17	—	—	VSS
29	23	18	—	—	USBDN
30	24	19	—	—	USBDP
31	25	20	—	—	VUSB33
32	26	21	PTG0	KBIP0	USB_ALT_CLK
33	27	22	PTG1	KBIP1	—
34	28	—	PTA0	RGPIO0	USB_SESSVLD
35	29	—	PTA1	RGPIO1	USB_SESSEND
36	30	—	PTA2	RGPIO2	USB_VBUSVLD
37	31	—	PTA3	RGPIO3	USB_PULLUP(D+)
38	32	—	PTA4	RGPIO4	USB_DM_DOWN
39	33	—	PTA5	RGPIO5	USB_DP_DOWN
40	—	—	PTA6	RGPIO6	USB_ID
41	—	—	PTA7	RGPIO7	—
42	34	23	PTB0	MISO2	ADP0
43	35	24	PTB1	MOSI2	ADP1
44	36	25	PTB2	SPSCK2	ADP2
45	37	26	PTB3	$\overline{SS2}$	ADP3
46	38	27	PTB4	KBIP4	ADP4
47	39	28	PTB5	KBIP5	ADP5
48	40	—	PTB6	ADP6	—

[3] 1s - Single Layer Board, one signal layer
[4] 2s2p - Four Layer Board, 2 signal and 2 power layers

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \quad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °Cθ_{JA} = Package thermal resistance, junction-to-ambient, °C/W$P_D = P_{int} + P_{I/O}$$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving equations 1 and 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving equations 1 and 2 iteratively for any value of T_A.

2.4 Electrostatic Discharge (ESD) Protection Characteristics

Although damage from static discharge is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with CDF-AEC-Q00 Stress Test Qualification for Automotive Grade Integrated Circuits. (http://www.aecouncil.com/) This device was qualified to AEC-Q100 Rev E.

A device is considered to have failed if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 8. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series Resistance	R1	1500	Ω
	Storage Capacitance	C	100	pF
	Number of Pulse per pin	–	3	
Latch-up	Minimum input voltage limit		–2.5	V
	Maximum input voltage limit		7.5	V

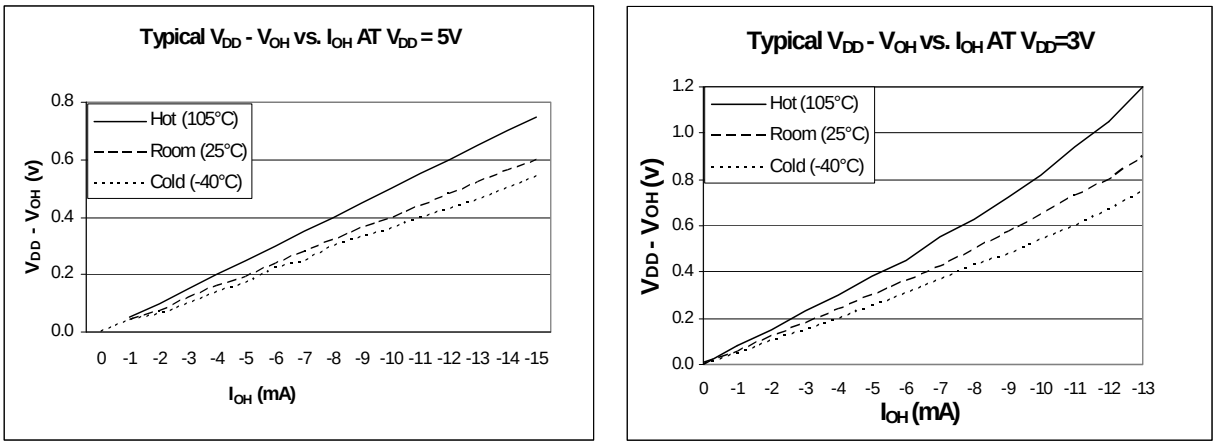


Figure 7. Typical High-side Drive (source) characteristics – High Drive (PTxDSn = 1)

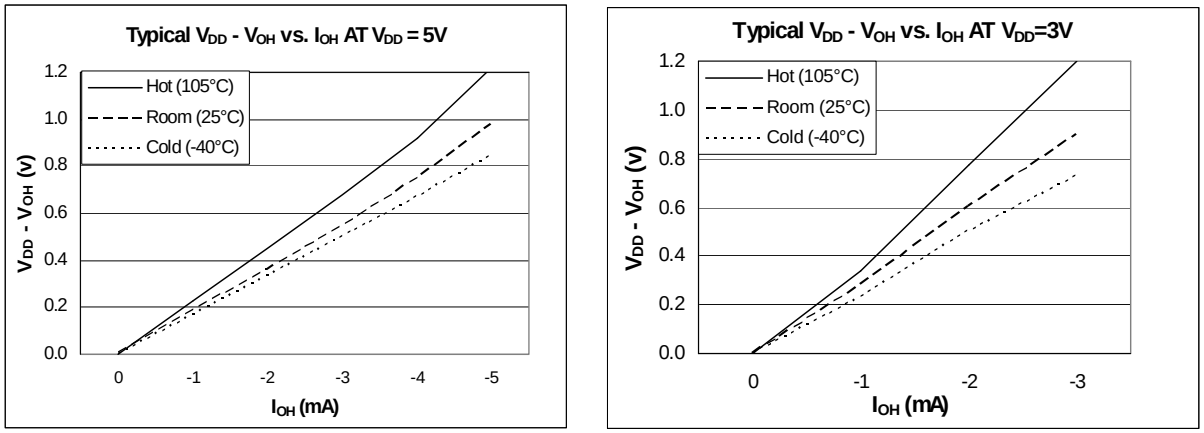


Figure 8. Typical High-side Drive (source) characteristics – Low Drive (PTxDSn = 0)

2.6 Supply Current Characteristics

Table 11. Supply Current Characteristics

Num	C	Parameter	Symbol	V_{DD} (V)	Typical[1]	Max[2]	Unit
1	C	Run supply current[3] measured at (CPU clock = 2 MHz, f_{Bus} = 1 MHz)	RI_{DD}	5	4.0	7	mA
				3	4.0	7	
2	P	Run supply current[3] measured at (CPU clock = 16 MHz, f_{Bus} = 8 MHz)		5	19	30	mA
				3	18.7	30	
3	C	Run supply current[3] measured at (CPU clock = 48 MHz, f_{Bus} = 24 MHz)		5	45	70	mA
				3	44	70	

Table 11. Supply Current Characteristics

Num	C	Parameter	Symbol	V_{DD} (V)	Typical[1]	Max[2]	Unit
4	C	Wait mode supply current[3] measured at (CPU clock = 2 MHz, f_{Bus} = 1 MHz)	WI_{DD}	5	2.03	3	mA
				3	2	3	
5	C	Wait mode supply current[3] measured at (CPU clock = 16 MHz, f_{Bus} = 8 MHz)		5	7.73	12	mA
				3	7.7	12	
6	C	Wait mode supply current[3] measured at (CPU clock = 48 MHz, f_{Bus} = 24 MHz)		5	22	30	mA
				3	21.9	30	
7	C	Stop2 mode supply current –40 °C 25 °C 105 °C	$S2I_{DD}$	5	1.35	3 3 35	µA
		–40 °C 25 °C 105 °C		3	1.25	3 3 35	µA
8	P	Stop3 mode supply current –40 °C 25 °C 105 °C	$S3I_{DD}$	5	1.41	3 3 35	µA
		–40 °C 25 °C 105 °C		3	1.35	3 3 35	µA
9	C	Stop4 mode supply current –40 °C 25 °C 105 °C	$S4I_{DD}$	5	106	200	µA
		–40 °C 25 °C 105 °C		3	96	200	µA
10	P	RTC adder to stop2 or stop3[4], 25°C	$S23I_{DDRTC}$	5	300	—	nA
				3	300	—	nA
11	P	Adder to stop3 for oscillator enabled[5] (ERCLKEN =1 and EREFSTEN = 1)	$S23I_{DDOSC}$	5	5	—	µA
				3	5	—	µA

1 Typicals are measured at 25°C.

2 Values given here are preliminary estimates prior to completing characterization.

3 All modules' clocks are switched on, code runs from flash, in FEI mode, and there are no DC loads on port pins.

4 Most customers are expected to find that auto-wakeup from stop2 or stop3 can be used instead of the higher current wait mode.

5 Values given under the following conditions: low range operation (RANGE = 0), low power mode (HGO = 0)

2.7 Analog Comparator (ACMP) Electricals

Table 12. Analog Comparator Electrical Specifications

Num	C	Rating	Symbol	Min	Typical	Max	Unit
1		Supply voltage	V_{DD}	2.7	—	5.5	V
2		Supply current (active)	I_{DDAC}	—	20	35	µA
3		Analog input voltage	V_{AIN}	V_{SS} – 0.3	—	V_{DD}	V
4		Analog input offset voltage	V_{AIO}		20	40	mV
5		Analog Comparator hysteresis	V_H	3.0	6.0	20.0	mV
6		Analog input leakage current	I_{ALKG}	--	--	1.0	µA
7		Analog Comparator initialization delay	t_{AINIT}	—	—	1.0	µs
8		Bandgap Voltage Reference Factory trimmed at V_{DD} = 3.0 V, Temp = 25°C	V_{BG}	1.19	1.20	1.21	V

2.8 ADC Characteristics

Table 13. 5 Volt 12-bit ADC Operating Conditions

Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
Supply voltage	Absolute	V_{DDA}	2.7	—	5.5	V	
	Delta to V_{DD} (V_{DD}-V_{DDA})[2]	ΔV_{DDA}	–100	0	+100	mV	
Ground voltage	Delta to V_{SS} (V_{SS}-V_{SSA})[2]	ΔV_{SSA}	–100	0	+100	mV	
Ref Voltage High		V_{REFH}	2.7	V_{DDA}	V_{DDA}	V	
Ref Voltage Low		V_{REFL}	V_{SSA}	V_{SSA}	V_{SSA}	V	
Input Voltage		V_{ADIN}	V_{REFL}	—	V_{REFH}	V	
Input Capacitance		C_{ADIN}	—	4.5	5.5	pF	
Input Resistance		R_{ADIN}	—	3	5	kΩ	
Analog Source Resistance	12 bit mode f_{ADCK} > 4MHz f_{ADCK} < 4MHz	R_{AS}	 — —	 — —	 2 5	kΩ	External to MCU
	10 bit mode f_{ADCK} > 4MHz f_{ADCK} < 4MHz		 — —	 — —	 5 10		
	8 bit mode (all valid f_{ADCK})		—	—	10		
ADC Conversion Clock Freq.	High Speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	
	Low Power (ADLPC=1)		0.4	—	4.0		

1 Typical values assume V_{DDA} = 5.0V, Temp = 25°C, f_{ADCK}=1.0MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 DC potential difference.

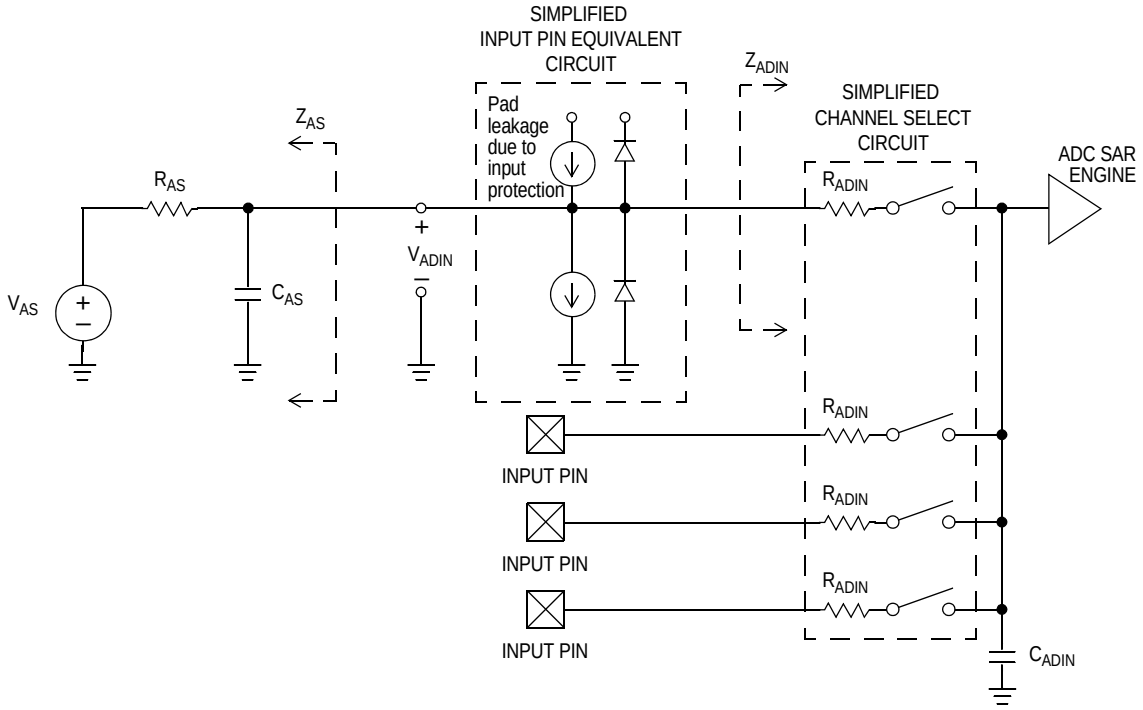


Figure 9. ADC Input Impedance Equivalency Diagram

Table 14. 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

Characteristic	Conditions	C	Symb	Min	Typ[1]	Max	Unit	Comment
Supply Current ADLPC=1 ADLSMP=1 ADCO=1		T	I_{DDAD}	—	133	—	µA	
Supply Current ADLPC=1 ADLSMP=0 ADCO=1		T	I_{DDAD}	—	218	—	µA	
Supply Current ADLPC=0 ADLSMP=1 ADCO=1		T	I_{DDAD}	—	327	—	µA	
Supply Current ADLPC=0 ADLSMP=0 ADCO=1		P	I_{DDAD}	—	0.582	1	mA	
Supply Current	Stop, Reset, Module Off		I_{DDAD}	—	0.011	1	µA	
ADC Asynchronous Clock Source	High Speed (ADLPC=0)	T	f_{ADACK}	2	3.3	5	MHz	t_{ADACK} = $1/f_{ADACK}$
	Low Power (ADLPC=1)			1.25	2	3.3		

5 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{BUS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

6 625 ns represents 5 time quanta for CAN applications, under worst case conditions of 8 MHz CAN bus clock, 1 Mbps CAN bus speed, and 8 time quanta per bit for bit time settings. 5 time quanta is the minimum time between a synchronization edge and the sample point of a bit using 8 time quanta per bit.

7 Below D_{lock} minimum, the MCG is guaranteed to enter lock. Above D_{lock} maximum, the MCG will not enter lock. But if the MCG is already in lock, then the MCG may stay in lock.

8 Below D_{unl} minimum, the MCG will not exit lock if already in lock. Above D_{unl} maximum, the MCG is guaranteed to exit lock.

2.11 AC Characteristics

This section describes ac timing characteristics for each peripheral system.

2.11.1 Control Timing

Table 17. Control Timing

Num	C	Parameter	Symbol	Min	Typ[1]	Max	Unit
1		Bus frequency ($t_{cyc} = 1/f_{Bus}$)	f_{Bus}	dc	—	24	MHz
2		Internal low-power oscillator period	t_{LPO}	700		1300	µs
3		External reset pulse width[2] ($t_{cyc} = 1/f_{Self\_reset}$)	t_{extrst}	100		—	ns
4		Reset low drive	t_{rstdrv}	66 x t_{cyc}		—	ns
5		Active background debug mode latch setup time	t_{MSSU}	500		—	ns
6		Active background debug mode latch hold time	t_{MSH}	100		—	ns
7		IRQ pulse width Asynchronous path[2] Synchronous path[3]	t_{ILIH}, t_{IHIL}	 100 1.5 x t_{cyc}	—	—	ns
8		KBIPx pulse width Asynchronous path[2] Synchronous path[3]	t_{ILIH}, t_{IHIL}	 100 1.5 x t_{cyc}	—	—	ns
9		Port rise and fall time (load = 50 pF)[4] Slew rate control disabled (PTxSE = 0) High drive Slew rate control enabled (PTxSE = 1) High drive Slew rate control disabled (PTxSE = 0) Low drive Slew rate control enabled (PTxSE = 1) Low drive	t_{Rise}, t_{Fall}	 — — 	 11 35 40 75		ns

1 Typical values are based on characterization data at V_{DD} = 5.0V, 25°C unless otherwise stated.

2 This is the shortest pulse guaranteed to be recognized as a reset pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

3 This is the minimum pulse width guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

4 Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range –40°C to 105°C.

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply.

Table 21. Flash Characteristics

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
1		Supply voltage for program/erase	$V_{prog/erase}$	2.7		5.5	V
2		Supply voltage for read operation	V_{Read}	2.7		5.5	V
3		Internal FCLK frequency[2]	f_{FCLK}	150		200	kHz
4		Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
5		Byte program time (random location)(2)	t_{prog}	9			t_{Fcyc}
6		Byte program time (burst mode)(2)	t_{Burst}	4			t_{Fcyc}
7		Page erase time[3]	t_{Page}	4000			t_{Fcyc}
8		Mass erase time(2)	t_{Mass}	20,000			t_{Fcyc}
9	C	Program/erase endurance[4] T_L to T_H = –40°C to + 105°C T = 25°C		10,000 —	— 100,000	— —	cycles
10		Data retention[5]	t_{D_ret}	15	100	—	years

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25°C unless otherwise stated.

2 The frequency of this clock is controlled by a software setting.

3 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

4 Typical endurance for Flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory*.

5 Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, Typical Data Retention for Nonvolatile Memory.

2.14 USB Electricals

The USB electricals for the USBOTG module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit http://www.usb.org.

If the Freescale USBOTG implementation requires additional or deviant electrical characteristics, this space would be used to communicate that information.

3 Mechanical Outline Drawings

3.1 80-pin LQFP

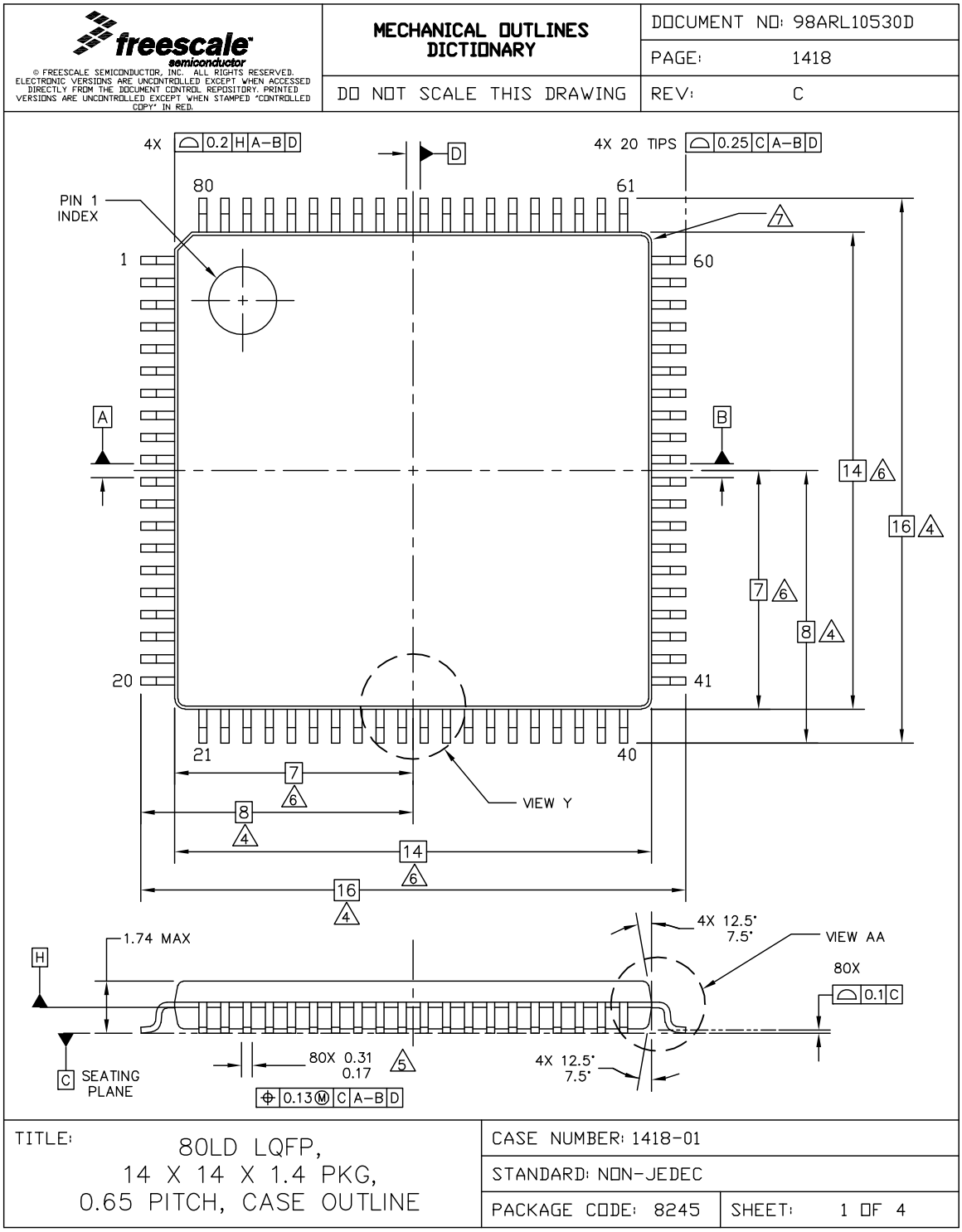


Figure 18. 80-pin LQFP Diagram - I

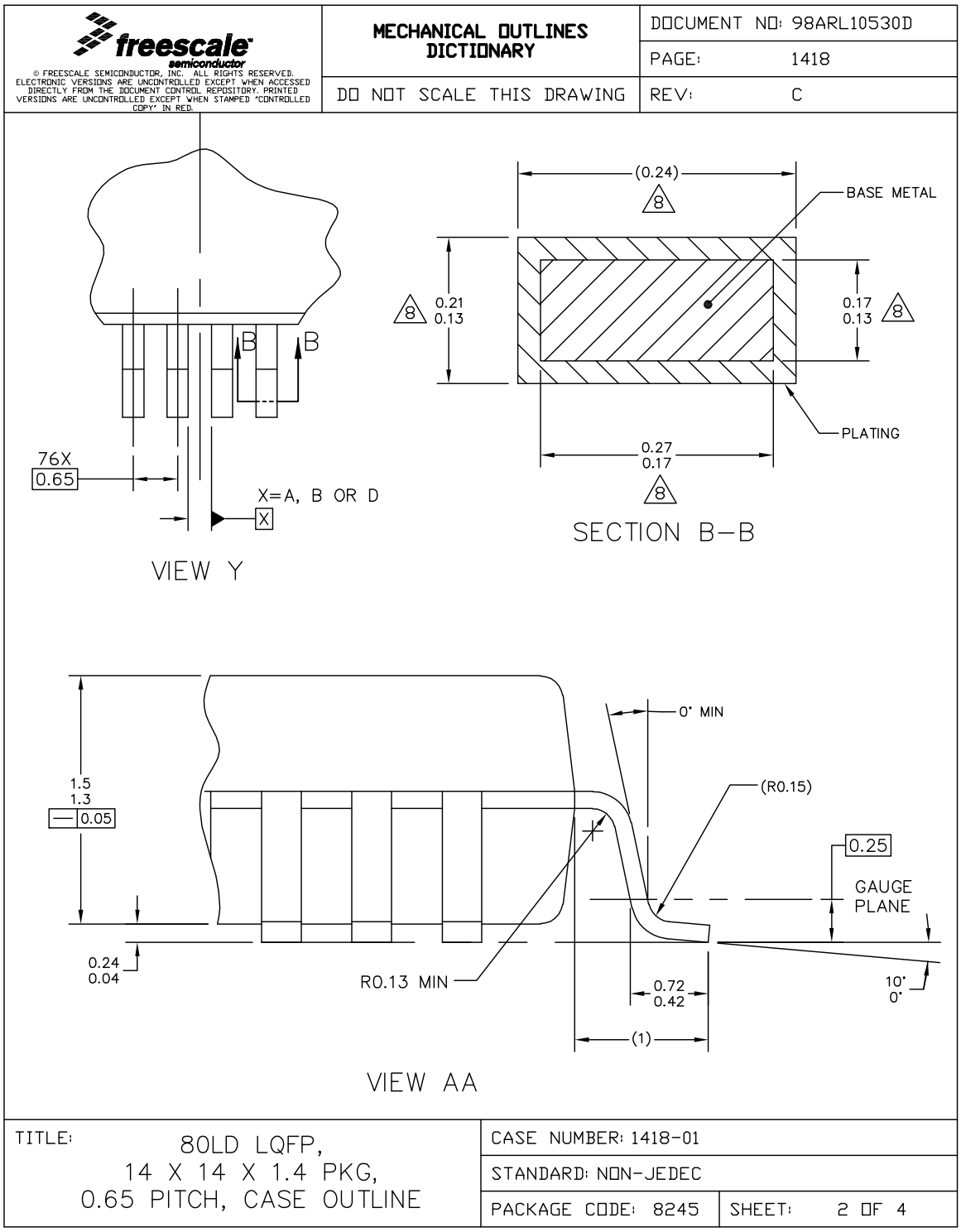
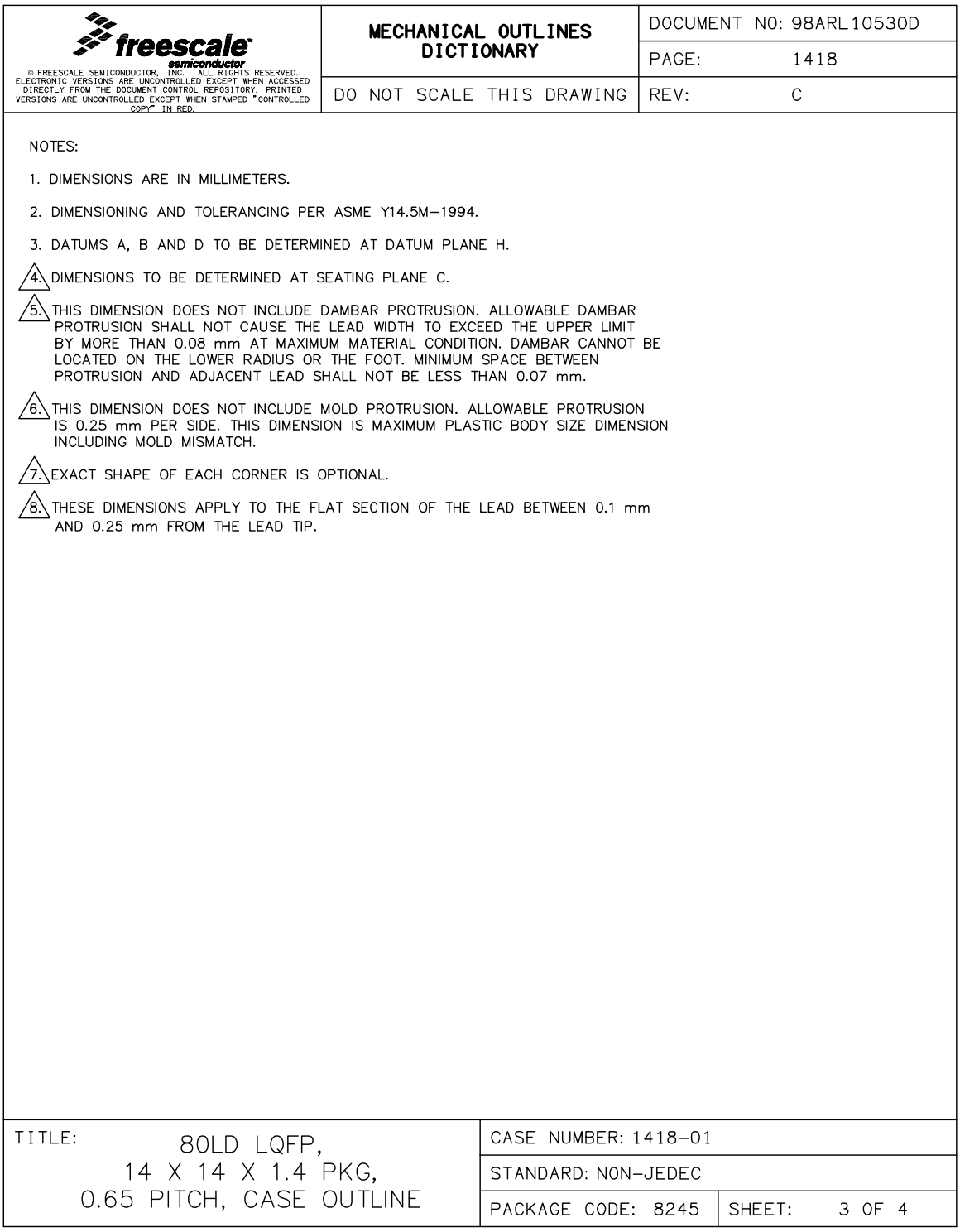


Figure 19. 80-pin LQFP Diagram - II



freescale semiconductor

MECHANICAL OUTLINES DICTIONARY

DOCUMENT NO: 98ARL10530D

PAGE: 1418

DO NOT SCALE THIS DRAWING

REV: C

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 mm AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 mm.
6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.
8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 mm AND 0.25 mm FROM THE LEAD TIP.

TITLE: 80LD LQFP, 14 X 14 X 1.4 PKG, 0.65 PITCH, CASE OUTLINE

CASE NUMBER: 1418–01

STANDARD: NON–JEDEC

PACKAGE CODE: 8245

SHEET: 3 OF 4

Figure 20. 80-pin LQFP Diagram - III

3.2 64-pin LQFP

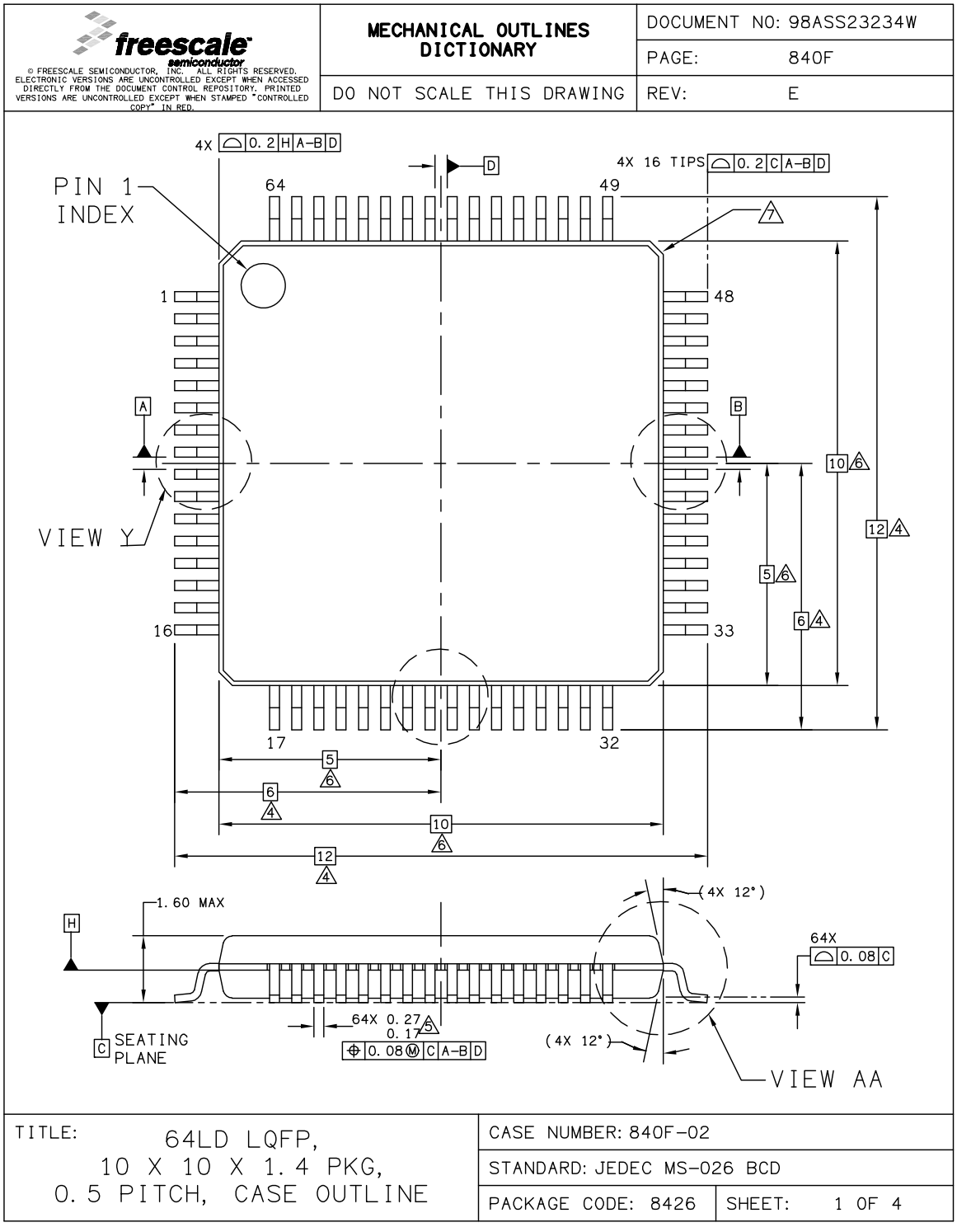


Figure 21. 64-pin LQFP Diagram - I

freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23234W
		PAGE: 840F
	DO NOT SCALE THIS DRAWING	REV: E

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 mm AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 mm.
6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.
8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 mm AND 0.25 mm FROM THE LEAD TIP.

TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F–02	
	STANDARD: JEDEC MS–026 BCD	
	PACKAGE CODE: 8426	SHEET: 3

Figure 23. 64-pin LQFP Diagram - III

3.4 44-pin LQFP

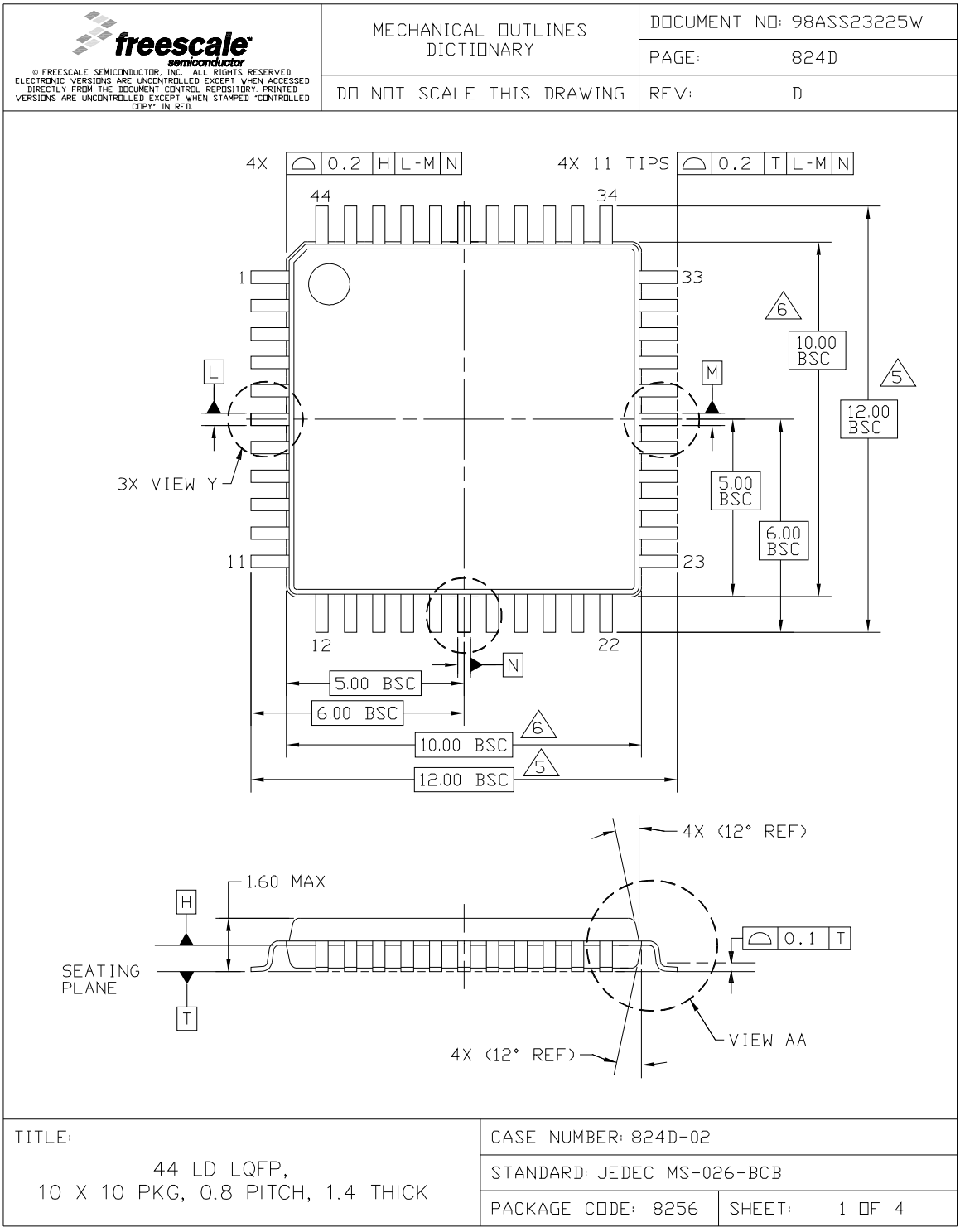


Figure 27. 44-pin LQFP Diagram - I

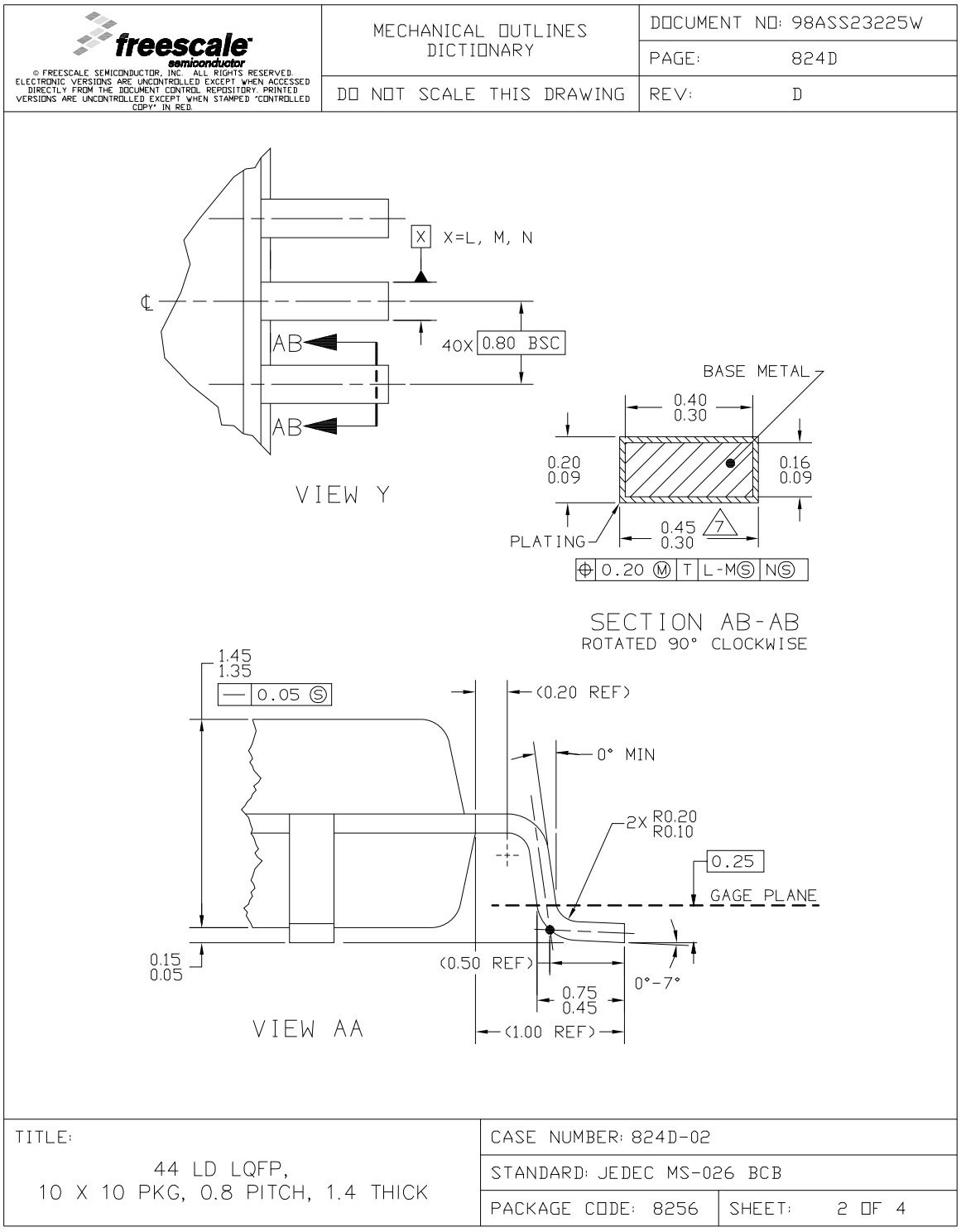


Figure 28. 44-pin LQFP Diagram - II

freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23225W
		PAGE: 824D
	DO NOT SCALE THIS DRAWING	REV: D

NOTES:

1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DATUM PLANE H IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DATUMS L, M AND N TO BE DETERMINED AT DATUM PLANE H.
5. DIMENSIONS TO BE DETERMINED AT SEATING PLANE T.
6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 PER SIDE. DIMENSIONS DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
7. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE DIMENSION TO EXCEED 0.53. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION 0.07.

TITLE: 44 LD LQFP, 10 X 10 PKG, 0.8 PITCH, 1.4 THICK	CASE NUMBER: 824D-02	
	STANDARD: JEDEC MS-026 BCB	
	PACKAGE CODE: 8256	SHEET: 3 OF 4

Figure 29. 44-pin LQFP Diagram - III